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## PATENT ABSTRACTS OF JAPAN

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(71) Applicant: MATSUSHITA ELECTRONICS CORP

(72) Inventor: ARIGA RIE

(74) Representative:

**(54) FLOATING-GATE TYPE  
NONVOLATILE MEMORY  
ELEMENT**

(57) Abstract:

**PURPOSE:** To not only project ultraviolet rays but also enable an erasing electrically on the erasing by combining a diode with a floating-gate.

**CONSTITUTION:** A diode is combined with a floating-gate. Consequently, when a diode 7 for the floating-gate section is biassed in the opposite direction, only a memory element section is effective in the floating-gate 4, and charges can be stored temporarily as a floating-gate type nonvolatile memory element. When the floating-gate 4 section is biassed in the forward direction, on the contrary, charges stored in the memory element section can be discharged.

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